

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (currently amended) Method ~~A method~~ of selective etching comprising:

[[-]] providing a first material selected from a group A on a substrate;

[[-]] providing a second material selected from a group B on a the substrate;

[[-]] selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant flowing across the substrate surface at a flow ~~sufficient~~ sufficiently fast to generate a mean velocity v parallel to the ~~substrate's~~ surface of the substrate of ~~minimum 0.1 m/s~~ at least 0.1 m/s.

2. (currently amended) Method ~~The method~~ of claim 1, wherein said liquid etchant is dispensed onto the substrate in a continuous flow and spread over the ~~substrate's~~ surface of the substrate.

3. (currently amended) Method ~~The method~~ of claim 2, wherein the point of impact of ~~the~~ a stream of said liquid

etchant stream is moved across the surface of the substrate in a time sequence.

4. **(currently amended)** ~~Method~~ The method of claim 2, wherein said liquid etchant is dispensed at a volume flow of at least ~~0,05~~ 0.05 l/min ~~(especially at least 0,5 l/min)~~.

5. **(currently amended)** ~~Method~~ The method of claim 1, wherein said substrate is rotated while exposed to said liquid etchant.

6. **(currently amended)** ~~Method~~ The method of claim 1, wherein group A comprises materials with a high dielectric constant.

7. **(currently amended)** ~~Method~~ The method of claim 1, wherein group B comprises silicon dioxide[[,]] and silicon.

8. **(currently amended)** ~~Method~~ The method of claim 1, wherein the second material is silicon dioxide and the liquid etchant comprises fluoride ions.

9. **(currently amended)** ~~Method~~ The method of claim 1, wherein said first material is ~~subjected a pretreatment in order~~

pretreated to damage the ~~material's~~ structure of said first material.

10. **(currently amended)** ~~Method~~ The method of claim 9, wherein said pretreatment is performed using an energetic particle bombardment.

11. **(currently amended)** ~~Method~~ The method of claim 1, wherein said liquid etchant is selected from ~~[[a]]~~ the group ~~comprising~~ consisting of:

[[-]] a solution comprising fluoride ions and an additive for lowering dielectric constant of said solution,

[[-]] an acidic[[,]] aqueous solution comprising fluoride ions[[.]]; and

[[-]] an acidic[[,]] aqueous solution comprising fluoride ions and an additive for lowering dielectric number ~~e.g.~~
~~an alcohol.~~

12. **(currently amended)** ~~Method~~ The method of claim 11, wherein said liquid etchant comprises an analytical concentration of less than ~~0.01~~ 0.01 mol/l of fluoride ions, wherein said analytical concentration is calculated as F⁻.

13. **(currently amended)** ~~Method~~ The method of claim 1, wherein said liquid etchant comprises fluoride ions and has a pH ~~value of below~~ less than 3.

14. **(new)** The method of claim 2, wherein the liquid etchant is dispensed at a volume flow of at least 0.5 l/min.

15. **(new)** The method of claim 11, wherein the additive for lowering dielectric number, in the acidic aqueous solution comprising fluoride ions, is an alcohol.

16. **(new)** A method of selective etching comprising selectively etching a first material on a substrate with a selectivity of at least 2:1 towards a second material on the substrate, by dispensing a liquid etchant flowing across the substrate surface at a flow sufficiently fast to generate a mean velocity v parallel to the surface of the substrate of at least 0.1 m/s.

17. (new) A method of selective etching comprising:
providing a first material on a substrate, wherein said first material is HfO_2 or ZrO_2 , and said first material is pretreated with an energetic particle bombardment;
providing a second material on the substrate; and
selectively etching said first material with a selectivity of at least 2:1 towards said second material by dispensing a liquid etchant flowing across the substrate surface at a flow sufficiently fast to generate a mean velocity v parallel to the surface of the substrate of at least 0.1 m/s.